T; 2004/09/28 16:13 GPUB;
PUB;
1
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T; 2004/09/28 16:54
SPUB;
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T; 2004/09/28 16:16
PUB;
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T; 2004/09/28 16:16
PUB;
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T; 2004/09/28 16:16
PUB;
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T; 2004/09/28 16:55
PUB; 2004/09/28 10.55
,, OD,
T; 2004/09/28 16:55
PUB;
" OB,
T; 2004/09/28 16:55
3PUB; 2004/09/28 10.55
n ob,
T; 2004/09/28 16:55
PUB; 2004/09/28 10:55
rob,
T; 2004/09/28 16:55
PUB;
Т; 2004/09/28 16:57
PUB; 2004/09/28 10:57
FOB,
T; 2004/09/28 16:57
PUB; 2004/09/28 16:57
TOB,
Т; 2004/09/28 16:57
SPUB; 2004/09/28 10.57
n OB,
Т; 2004/09/28 16:57
PUB;
,, OB,
Т; 2004/09/28 16:58
PUB;
1 OD,
Γ; 2004/09/28 16:59
PUB; 2004/09/28 10.39
1 00,
Г; 2004/09/28 16:59
PUB; 2004/09/28 10.59
1 UD,

L Number	Hits	Search Text	DB	Time stamp
1	1055	mosfet\$1 with jfet\$1	USPAT;	2004/09/28 20:08
			US-PGPUB;	
			JPO	
2	80942	gate adj (oxide or dielectric or insulat\$3)	USPAT;	2004/09/28 19:15
			US-PGPUB;	
	461		ЛРО	
3	461	"without" adj2 (gate adj (oxide or dielectric or insulat\$3))	USPAT;	2004/09/28 19:15
			US-PGPUB; JPO	
4	0	(mosfet\$1 with jfet\$1) and ("without" adj2 (gate adj (oxide or dielectric	USPAT;	2004/09/28 19:20
-	U	or insulat\$3)))	US-PGPUB;	2004/09/28 19.20
			ло	
5	41	(mosfet\$1 with jfet\$1) same (gate adj (oxide or dielectric or insulat\$3))	USPAT;	2004/09/28 19:50
		(8.5.5.5)	US-PGPUB;	20003
			JPO	
7	6219	vertical near2 (transistor\$1)	USPAT;	2004/09/28 20:10
			US-PGPUB;	
_			ЛО	
8	6169	jfet\$1 or (junction-fet\$1) or (junction adj fet\$1) or (junction adj field adj	USPAT;	2004/09/28 19:51
		effect)	US-PGPUB;	
9	120	(vertical near2 (transistor\$1)) same (jfet\$1 or (junction-fet\$1) or	ЛО	2004/00/20 20 02
1	120	(vertical hearz (dansistors)) same (hets) or (function-lets) or (junction adj fet\$1) or (junction adj field adj effect))	USPAT; US-PGPUB;	2004/09/28 20:02
		(Junetion and 10.61) of (Junetion and filed and effect))	ло Ло	
13	150893	mosfet\$1 or mos or (metal adj oxide adj semiconduct\$3)	USPAT;	2004/09/28 20:10
		(mem any country)	US-PGPUB;	200 1/05/20 20:10
!			ло	
14	2121	(jfet\$1 or (junction-fet\$1) or (junction adj fet\$1) or (junction adj field	USPAT;	2004/09/28 20:10
		adj effect)) same (mosfet\$1 or mos or (metal adj oxide adj	US-PGPUB;	
		semiconduct\$3))	JPO	
15	164	(vertical near2 (transistor\$1)) and ((jfet\$1 or (junction-fet\$1) or	USPAT;	2004/09/28 20:10
		(junction adj fet\$1) or (junction adj field adj effect)) same (mosfet\$1 or	US-PGPUB;	
16	80	mos or (metal adj oxide adj semiconduct\$3))) ((vertical near2 (transistor\$1)) and ((jfet\$1 or (junction-fet\$1) or	JPO	2004/00/29 20:10
10	80	(vertical leaf 2 (transistors)) and (thets) or (function-lets) or (junction adj fet\$1) or (junction adj fet\$1) or (junction adj fet\$1) or (junction adj fet\$1) and (thets) or (junction-lets) or	USPAT; US-PGPUB;	2004/09/28 20:10
		mos or (metal adj oxide adj semiconduct\$3)))) not (((mosfet\$1 with	лоз-гогов, ЛО	
		jfet\$1) same (gate adj (oxide or dielectric or insulat\$3))) or ((vertical	31 O	
		near2 (transistor\$1)) same (jfet\$1 or (junction-fet\$1) or (junction adj		
		fet\$1) or (junction adj field adj effect))))		